



FCPF250N65S3R0L

N-Channel SuperFET® III MOSFET

650 V, 12 A, 250 mΩ

Features

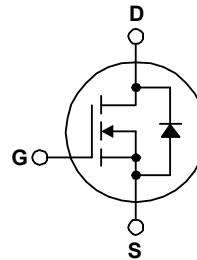
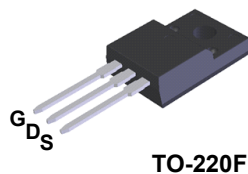
- 700 V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 210\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 24\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 248\text{ pF}$)
- 100% Avalanche Tested
- RoHS Compliant

Applications

- Computing / Display Power Supplies
- Telecom / Server Power Supplies
- Industrial Power Supplies

Description

SuperFET® III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate. Consequently, SuperFET III MOSFET is very suitable for various power system for miniaturization and higher efficiency.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FCPF250N65S3R0L	Unit
V_{DSS}	Drain to Source Voltage	650	V
V_{GSS}	Gate to Source Voltage	- DC	± 30
		- AC ($f > 1\text{ Hz}$)	± 30
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	12*
		- Continuous ($T_C = 100^\circ\text{C}$)	7.6*
I_{DM}	Drain Current	- Pulsed (Note 1)	30*
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	57
I_{AS}	Avalanche Current	(Note 1)	2.3
E_{AR}	Repetitive Avalanche Energy	(Note 1)	0.31
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt	(Note 3)	
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	31
		- Derate Above 25°C	0.25
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

*Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FCPF250N65S3R0L	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	4.07	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCPF250N65S3R0L	FCPF250N65S3R0	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
--------	-----------	-----------------	------	------	------	------

Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	650	-	-	V
		$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 150^\circ\text{C}$	700	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 1\text{ mA}$, Referenced to 25°C	-	0.67	-	$V/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 520\text{ V}, T_C = 125^\circ\text{C}$	-	0.77	-	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1.2\text{ mA}$	2.5	-	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 6\text{ A}$	-	210	250	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 20\text{ V}, I_D = 6\text{ A}$	-	7.4	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	1010	-	pF
C_{oss}	Output Capacitance		-	25	-	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$	-	248	-	pF
$C_{oss(er.)}$	Energy Related Output Capacitance	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$	-	33	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 400\text{ V}, I_D = 6\text{ A}, V_{GS} = 10\text{ V}$ (Note 4)	-	24	-	nC
Q_{gs}	Gate to Source Gate Charge		-	6.1	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	9.7	-	nC
ESR	Equivalent Series Resistance	$f = 1\text{ MHz}$	-	1.1	-	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 400\text{ V}, I_D = 6\text{ A}, V_{GS} = 10\text{ V}, R_g = 4.7\ \Omega$ (Note 4)	-	15	-	ns
t_r	Turn-On Rise Time		-	13	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	40	-	ns
t_f	Turn-Off Fall Time		-	7.2	-	ns

Source-Drain Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	12	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	30	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_{SD} = 6\text{ A}$	-	-	1.2	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_{SD} = 6\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$	-	251	-	ns
Q_{rr}	Reverse Recovery Charge		-	3.4	-	μC

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $I_{AS} = 2.3\text{ A}, R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 6\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq 400\text{ V}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

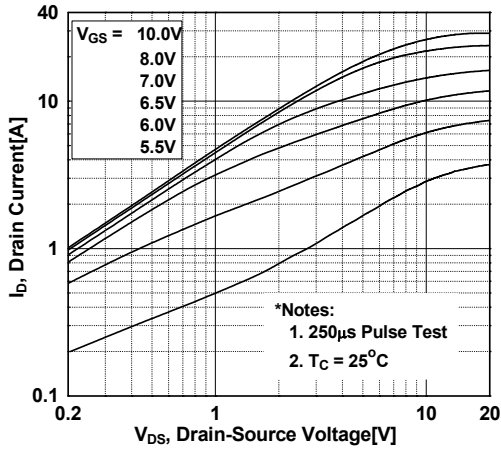


Figure 2. Transfer Characteristics

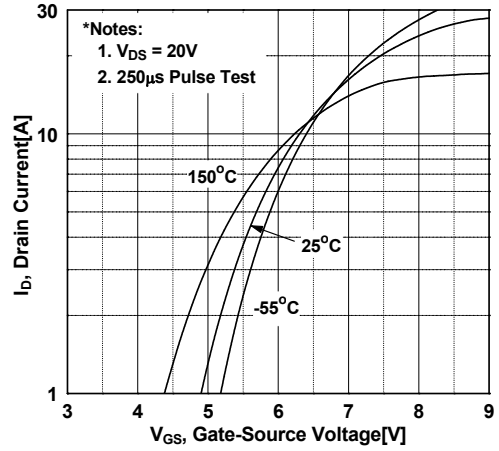


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

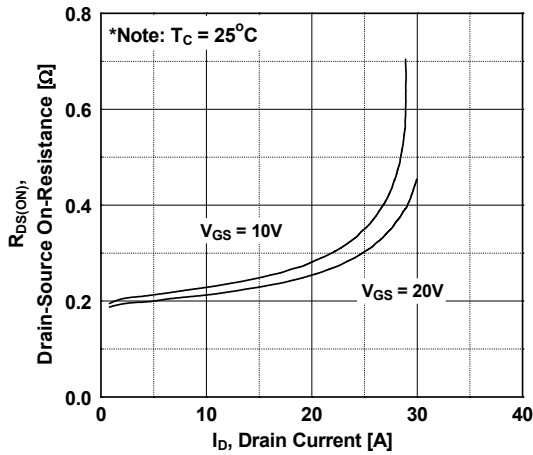


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

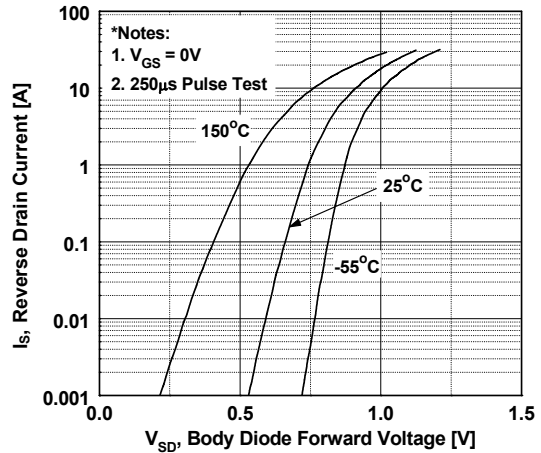


Figure 5. Capacitance Characteristics

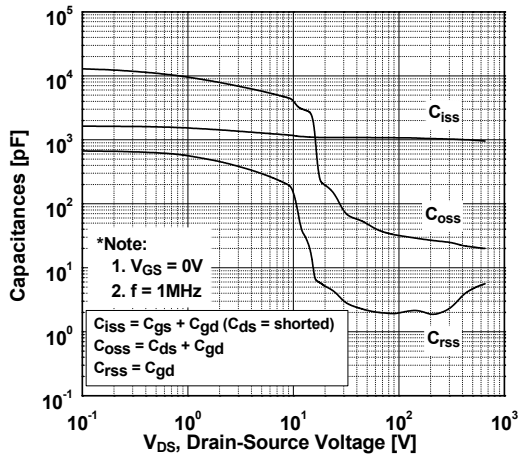
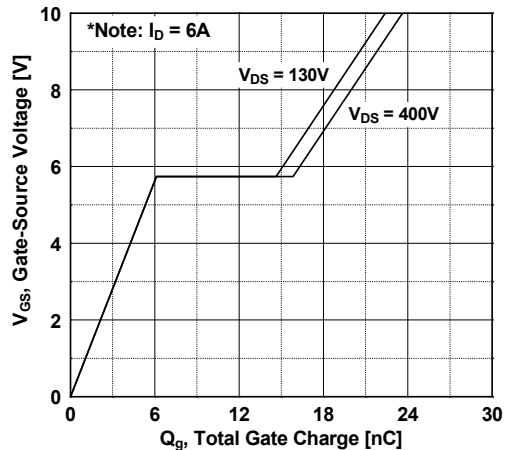


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

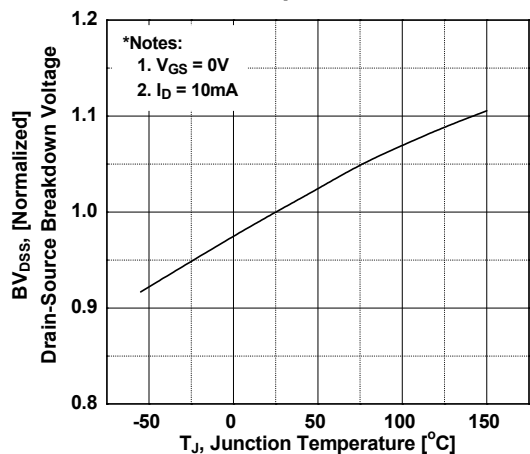


Figure 8. On-Resistance Variation vs. Temperature

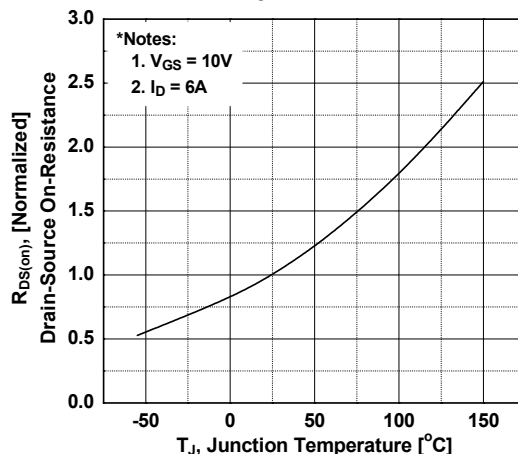


Figure 9. Maximum Safe Operating Area

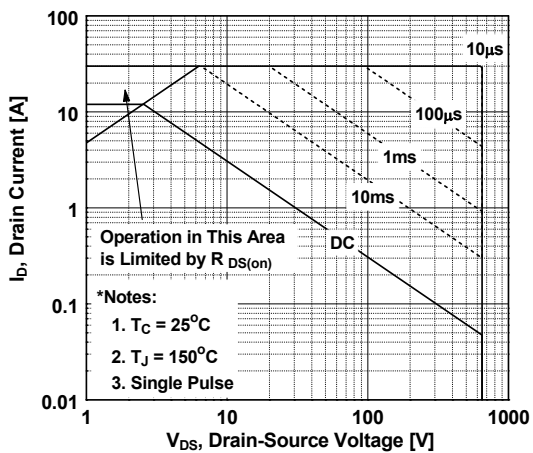


Figure 10. Maximum Drain Current vs. Case Temperature

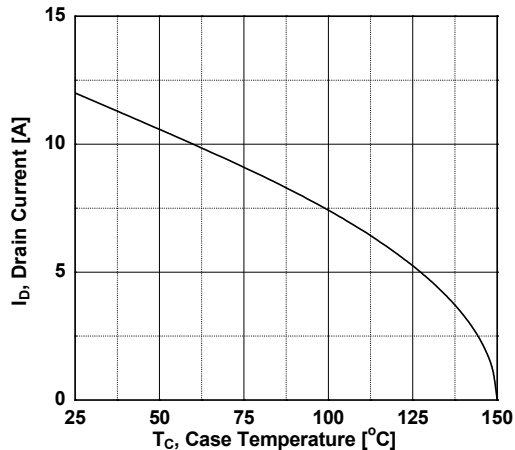
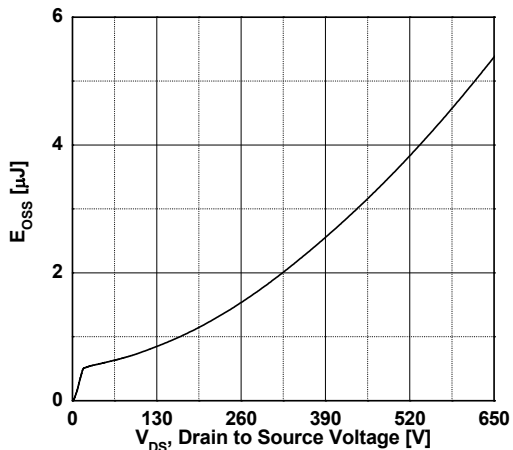
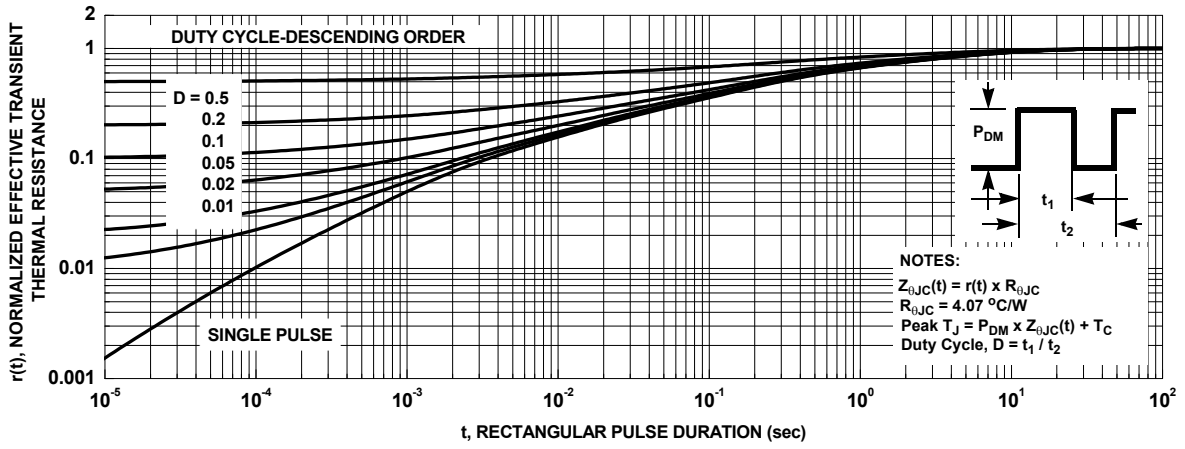


Figure 11. Eoss vs. Drain to Source Voltage



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



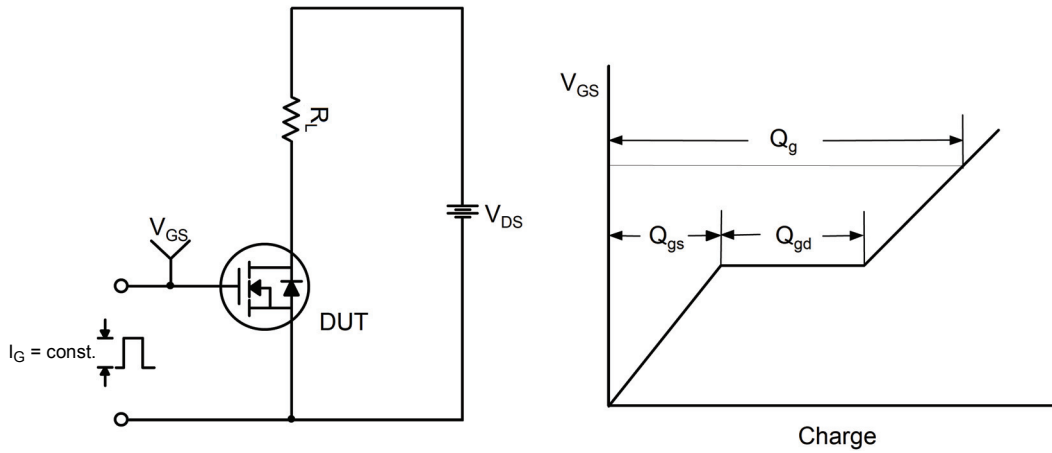


Figure 13. Gate Charge Test Circuit & Waveform



Figure 14. Resistive Switching Test Circuit & Waveforms

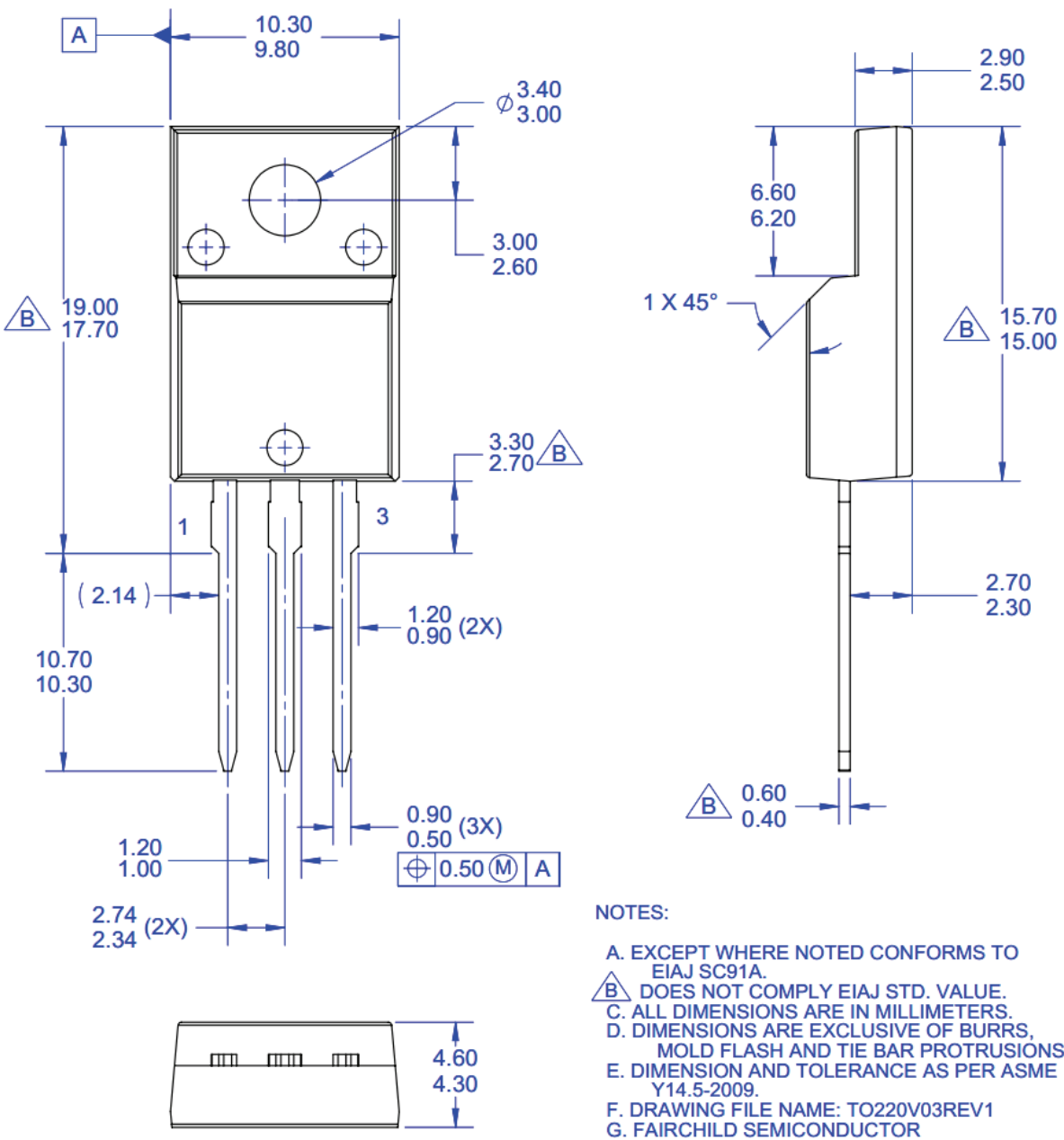


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms



Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



ON Semiconductor and the ON Logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.